
HM5164165A Series HM5165165A Series

4194304-word $\times$ 16-bit Dynamic RAM

HITACHI

ADE-203-453 (Z)
Preliminary - Rev. 0.4
Apr. 28, 1997

Description

The Hitachi HM5164165A Series, HM5165165A Series are CMOS dynamic RAMs organized as 4,194,304-word $\times$ 16-bit. They employ the most advanced CMOS technology for high performance and low power. HM5164165A Series, HM5165165A Series offer Extended Data Out (EDO) Page Mode as a high speed access mode. They have the package variations of standard 400 mil 50-pin plastic SOJ and standard 400 mil 50-pin plastic TSOPII

Features

- Single 3.3 V (± 0.3 V)
- Access time: 50 ns/60 ns/70 ns (max)
- Power dissipation
 - Active mode : TBD/450 mW/378 mW (max) (HM5164165A Series)
: TBD/648 mW/558 mW (max) (HM5165165A Series)
 - Standby mode : 7.2 mW (max)
: 0.72 mW (max) (L-version)
- EDO page mode capability
- Refresh cycles
 - $\overline{\text{RAS}}$ -only refresh
 - 8192 cycles/64 ms (HM5164165A)
 - 4096 cycles/64 ms (HM5165165A)
/128 ms (HM5165165AL) (L-version)
 - CBR/Hidden refresh
 - 4096 cycles/64 ms (HM5164165A, HM5165165A)
/128 ms (HM5165165AL) (L-version)
- 4 variations of refresh
 - $\overline{\text{RAS}}$ -only refresh
 - $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh
 - Hidden refresh
 - Self refresh (L-version)

■ 4496203 0033210 779 ■

HM5164165A/HM5165165A Series

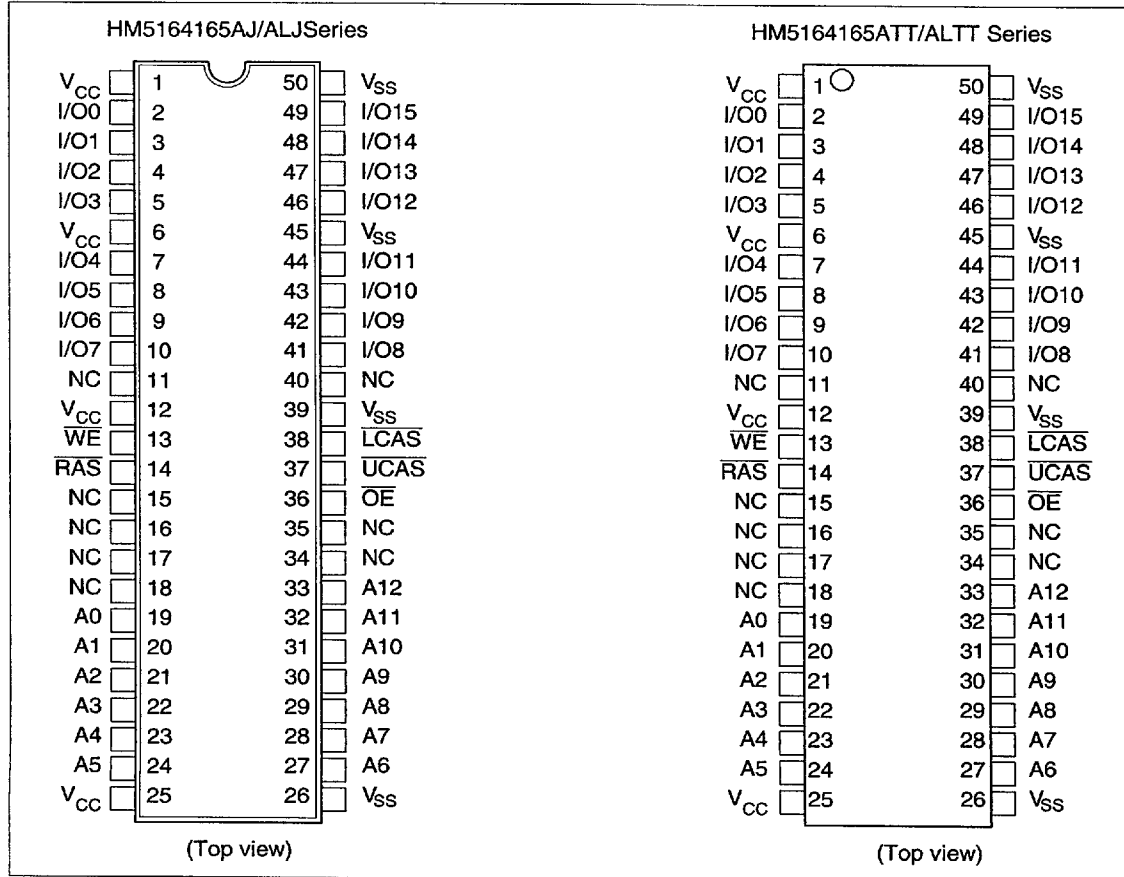
- $\overline{2CAS}$ -byte control
- Battery backup operation (L-version)

Ordering Information

Type No.	Access time	Package
HM5164165AJ-5	50 ns	400-mil 50-pin plastic SOJ (CP-50DA)
HM5164165AJ-6	60 ns	
HM5164165AJ-7	70 ns	
HM5164165ALJ-5	50 ns	
HM5164165ALJ-6	60 ns	
HM5164165ALJ-7	70 ns	
HM5165165AJ-5	50 ns	
HM5165165AJ-6	60 ns	
HM5165165AJ-7	70 ns	
HM5165165ALJ-5	50 ns	
HM5165165ALJ-6	60 ns	
HM5165165ALJ-7	70 ns	
HM5164165ATT-5	50 ns	400-mil 50-pin plastic TSOP II (TTP-50DB)
HM5164165ATT-6	60 ns	
HM5164165ATT-7	70 ns	
HM5164165ALTT-5	50 ns	
HM5164165ALTT-6	60 ns	
HM5164165ALTT-7	70 ns	
HM5165165ATT-5	50 ns	
HM5165165ATT-6	60 ns	
HM5165165ATT-7	70 ns	
HM5165165ALTT-5	50 ns	
HM5165165ALTT-6	60 ns	
HM5165165ALTT-7	70 ns	

HM5164165A/HM5165165A Series

Pin Arrangement



Pin Description

Pin name	Function
A0 to A12	Address input - Row/Refresh address: A0 to A12 - Column address: A0 to A8
I/O0 to I/O15	Data input/Data output
$\overline{\text{RAS}}$	Row address strobe
$\overline{\text{UCAS}}, \overline{\text{LCAS}}$	Column address strobe
$\overline{\text{WE}}$	Read/Write enable
$\overline{\text{OE}}$	Output enable
V_{CC}	Power supply
V_{SS}	Ground

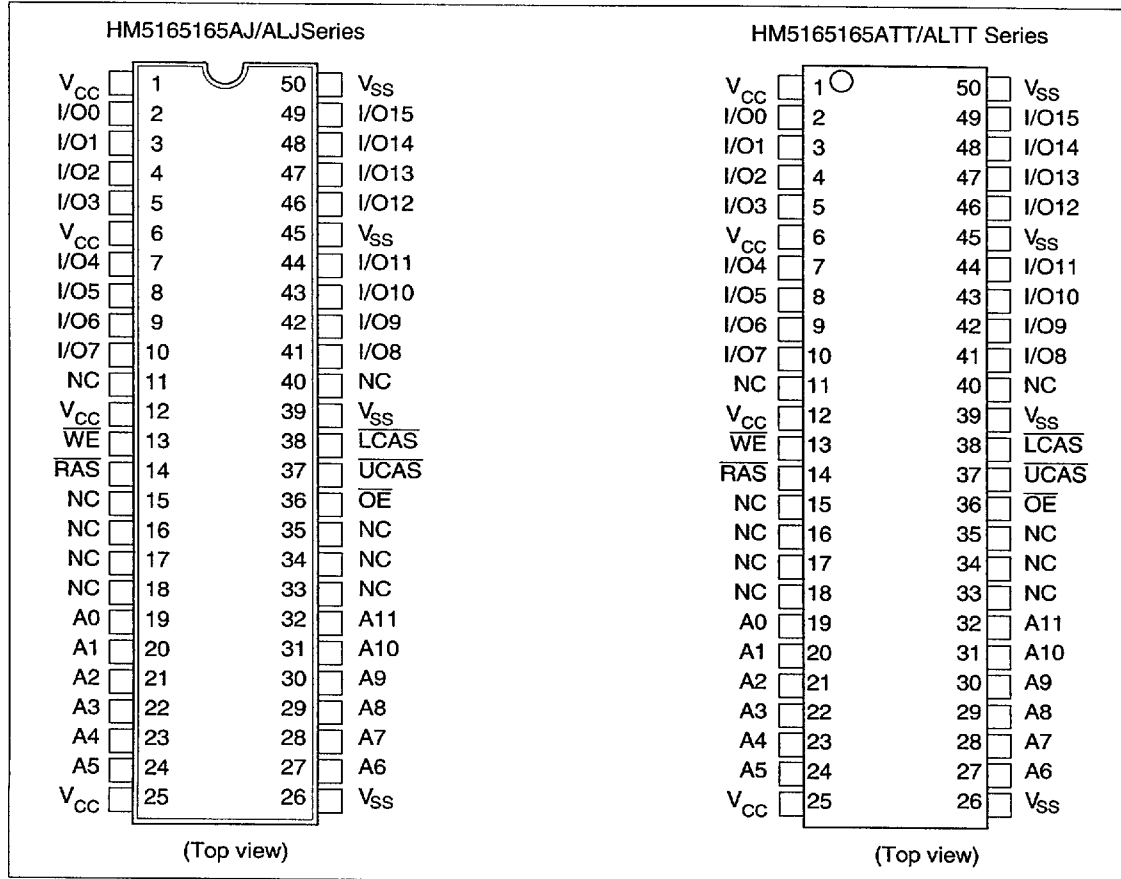
HITACHI

HM5164165A/HM5165165A Series

Pin name	Function
NC	No connection

HM5164165A/HM5165165A Series

Pin Arrangement



Pin Description

Pin name	Function
A0 to A11	Address input - Row/Refresh address: A0 to A11 - Column address: A0 to A9
I/O0 to I/O15	Data input/Data output
RAS	Row address strobe
UCAS, LCAS	Column address strobe
WE	Read/Write enable
OE	Output enable
V _{CC}	Power supply
V _{SS}	Ground

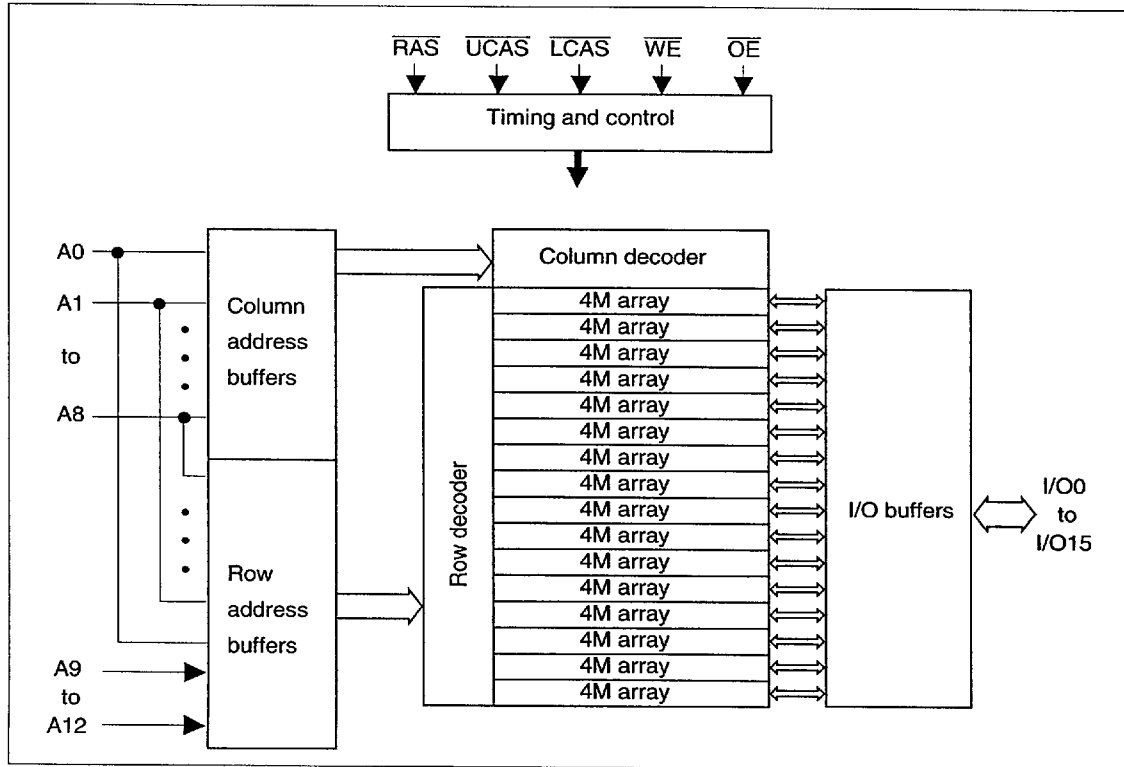
HITACHI

HM5164165A/HM5165165A Series

Pin name	Function
NC	No connection

HM5164165A/HM5165165A Series

Block Diagram (HM5164165A Series)



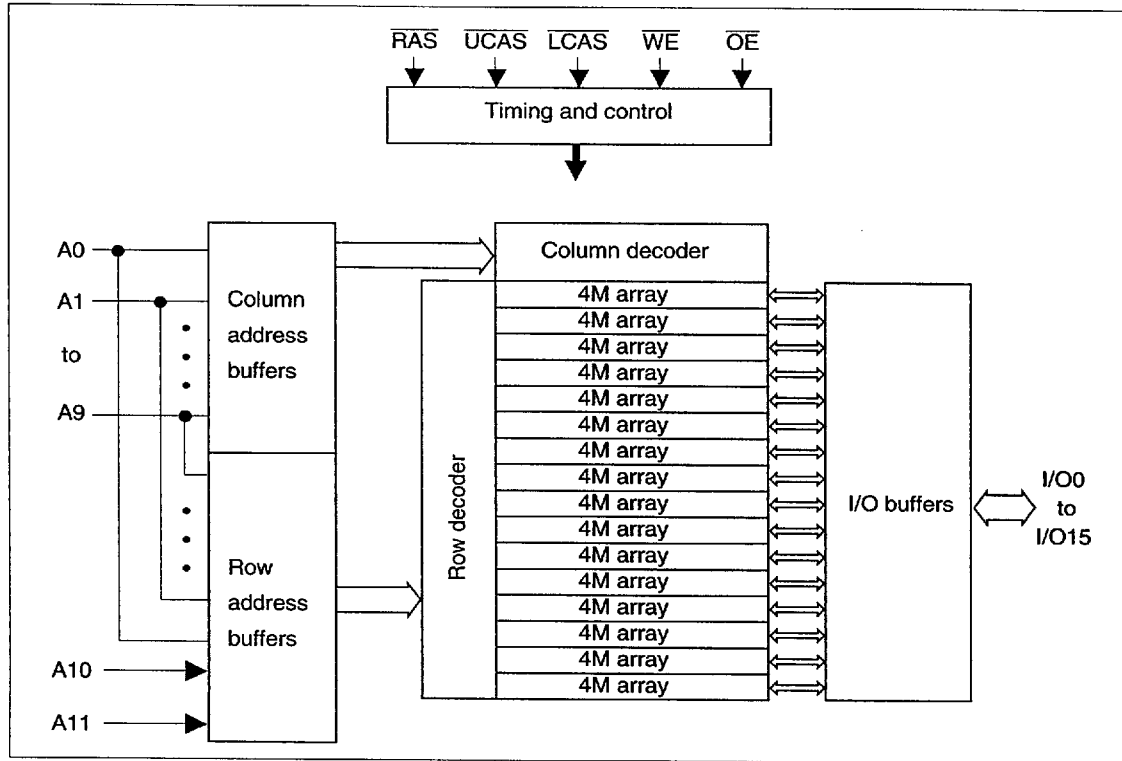
HITACHI

7

4496203 0033216 197

HM5164165A/HM5165165A Series

Block Diagram (HM5165165A Series)



HM5164165A/HM5165165A Series

Truth Table

$\overline{\text{RAS}}$	$\overline{\text{LCAS}}$	$\overline{\text{UCAS}}$	$\overline{\text{WE}}$	$\overline{\text{OE}}$	Output		Operation
H	D	D	D	D	Open		Standby
L	L	H	H	L	Valid	Lower byte	Read cycle
L	H	L	H	L	Valid	Upper byte	
L	L	L	H	L	Valid	Word	
L	L	H	L* ²	D	Open	Lower byte	Early write cycle
L	H	L	L* ²	D	Open	Upper byte	
L	L	L	L* ²	D	Open	Word	
L	L	H	L* ²	H	Undefined	Lower byte	Delayed write cycle
L	H	L	L* ²	H	Undefined	Upper byte	
L	L	L	L* ²	H	Undefined	Word	
L	L	H	H to L	L to H	Valid	Lower byte	Read-modify-write cycle
L	H	L	H to L	L to H	Valid	Upper byte	
L	L	L	H to L	L to H	Valid	Word	
L	H	H	D	D	Open	Word	$\overline{\text{RAS}}$ -only refresh cycle
H to L	H	L	H	D	Open	Word	$\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycle or
H to L	L	H	H	D	Open	Word	Self refresh cycle (L-version)
H to L	L	L	H	D	Open	Word	
L	L	L	H	H	Open		Read cycle (Output disabled)

Notes: 1. H: High (inactive) L: Low (active) D: H or L

2. $t_{\text{WCS}} \geq 0 \text{ ns}$ Early write cycle

$t_{\text{WCS}} < 0 \text{ ns}$ Delayed write cycle

3. Mode is determined by the OR function of the $\overline{\text{UCAS}}$ and $\overline{\text{LCAS}}$. (Mode is set by the earliest of $\overline{\text{UCAS}}$ and $\overline{\text{LCAS}}$ active edge and reset by the latest of $\overline{\text{UCAS}}$ and $\overline{\text{LCAS}}$ inactive edge.) However write OPERATION and output HIZ control are done independently by each $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$.

ex. if $\overline{\text{RAS}} = \text{H to L}$, $\overline{\text{UCAS}} = \text{H}$, $\overline{\text{LCAS}} = \text{L}$, then $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycle is selected.

HITACHI

HM5164165A/HM5165165A Series

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to V_{SS}	V_T	-0.5 to $V_{CC} + 0.5$ (≤ 4.6 V (max))	V
Supply voltage relative to V_{SS}	V_{CC}	-0.5 to $+4.6$	V
Short circuit output current	I_{out}	50	mA
Power dissipation	P_T	1.0	W
Operating temperature	T_{opr}	0 to $+70$	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to $+125$	$^{\circ}\text{C}$

Recommended DC Operating Conditions ($T_a = 0$ to $+70^{\circ}\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Supply voltage	V_{CC}	3.0	3.3	3.6	V	1, 2
Input high voltage	V_{IH}	2.0	—	$V_{CC} + 0.3$	V	1
Input low voltage	V_{IL}	-0.3	—	0.8	V	1

Notes: 1. All voltage referred to V_{SS} .

2. The supply voltage with all V_{CC} pins must be on the same level. The supply voltage with all V_{SS} pins must be on the same level.

HM5164165A/HM5165165A Series

DC Characteristics

(Ta = 0 to +70°C, V_{CC} = 3.3 V ± 0.3 V, V_{SS} = 0 V) (HM5164165A Series)

		HM5164165A							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Test conditions
Operating current ^{*1, *2}	I _{CC1}	—	TBD	—	125	—	105	mA	t _{RC} = min
Standby current	I _{CC2}	—	TBD	—	2	—	2	mA	TTL interface RAS, UCAS, LCAS = VIH Dout = High-Z
		—	TBD	—	1	—	1	mA	CMOS interface RAS, UCAS, LCAS ≥ V _{CC} - 0.2 V Dout = High-Z
Standby current (L-version)	I _{CC2}	—	TBD	—	TBD	—	TBD	μA	CMOS interface RAS, UCAS, LCAS ≥ V _{CC} - 0.2 V Dout = High-Z
RAS-only refresh current ^{*2}	I _{CC3}	—	TBD	—	125	—	105	mA	t _{RC} = min
Standby current ^{*1}	I _{CC5}	—	TBD	—	5	—	5	mA	RAS = V _{IH} UCAS, LCAS = V _{IL} Dout = enable
CAS-before-RAS refresh current	I _{CC6}	—	TBD	—	140	—	120	mA	t _{RC} = min
EDO page mode current ^{*1, *3}	I _{CC7}	—	TBD	—	120	—	105	mA	t _{HPC} = min
Battery backup current ^{*4} (Standby with CBR refresh) (L-version)	I _{CC10}	—	TBD	—	TBD	—	TBD	μA	CMOS interface Dout = High-Z CBR refresh: t _{RC} = 31.3 μs t _{RAS} ≤ 0.3 μs
Self refresh mode current (L-version)	I _{CC11}	—	TBD	—	TBD	—	TBD	μA	CMOS interface RAS, UCAS, LCAS ≤ 0.2 V Dout = High-Z
Input leakage current	I _{LI}	TBD	TBD	-10	10	-10	10	μA	0 V ≤ Vin ≤ V _{CC} + 0.3 V
Output leakage current	I _{LO}	TBD	TBD	-10	10	-10	10	μA	0 V ≤ Vout ≤ V _{CC} Dout = disable
Output high voltage	V _{OH}	TBD	TBD	2.4	V _{CC}	2.4	V _{CC}	V	High Iout = -2 mA
Output low voltage	V _{OL}	TBD	TBD	0	0.4	0	0.4	V	Low Iout = 2 mA

Notes: 1. I_{CC} depends on output load condition when the device is selected. I_{CC} max is specified at the output open condition.

2. Address can be changed once or less while RAS = V_{IL}.

3. Address can be changed once or less within one page mode cycle t_{HPC}.

4. V_{IH} ≥ V_{CC} - 0.2 V, 0 V ≤ V_{IL} ≤ 0.2 V.

HITACHI

HM5164165A/HM5165165A Series

DC Characteristics

(Ta = 0 to +70°C, V_{CC} = 3.3 V ± 0.3 V, V_{SS} = 0 V) (HM5165165A Series)

		HM5165165A							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Test conditions
Operating current*1, *2	I _{CC1}	—	TBD	—	180	—	155	mA	t _{RC} = min
Standby current	I _{CC2}	—	TBD	—	2	—	2	mA	TTL interface RAS, UCAS, LCAS = V _{IH} Dout = High-Z
		—	TBD	—	1	—	1	mA	CMOS interface RAS, UCAS, LCAS ≥ V _{CC} − 0.2 V Dout = High-Z
Standby current (L-version)	I _{CC2}	—	TBD	—	200	—	200	μA	CMOS interface RAS, UCAS, LCAS ≥ V _{CC} − 0.2 V Dout = High-Z
RAS-only refresh current*2	I _{CC3}	—	TBD	—	180	—	155	mA	t _{RC} = min
Standby current*1	I _{CC5}	—	TBD	—	5	—	5	mA	RAS = V _{IH} UCAS, LCAS = V _{IL} Dout = enable
CAS-before-RAS refresh current	I _{CC6}	—	TBD	—	140	—	120	mA	t _{RC} = min
EDO page mode current*1, *3	I _{CC7}	—	TBD	—	150	—	135	mA	t _{HPC} = min
Battery backup current*4 (Standby with CBR refresh) (L-version)	I _{CC10}	—	TBD	—	650	—	650	μA	CMOS interface Dout = High-Z CBR refresh: t _{RC} = 31.3 μs t _{RAS} ≤ 0.3 μs
Self refresh mode current (L-version)	I _{CC11}	—	TBD	—	500	—	500	μA	CMOS interface RAS, UCAS, LCAS ≤ 0.2 V Dout = High-Z
Input leakage current	I _I	TBD	TBD	−10	10	−10	10	μA	0 V ≤ Vin ≤ V _{CC} + 0.3 V
Output leakage current	I _{LO}	TBD	TBD	−10	10	−10	10	μA	0 V ≤ Vout ≤ V _{CC} Dout = disable
Output high voltage	V _{OH}	TBD	TBD	2.4	V _{CC}	2.4	V _{CC}	V	High Iout = −2 mA
Output low voltage	V _{OL}	TBD	TBD	0	0.4	0	0.4	V	Low Iout = 2 mA

Notes: 1. I_{CC} depends on output load condition when the device is selected. I_{CC} max is specified at the output open condition.

2. Address can be changed once or less while RAS = V_{IL}.

3. Address can be changed once or less within one page mode cycle t_{HPC}.

4. V_{IH} ≥ V_{CC} - 0.2 V, 0 V ≤ V_{IL} ≤ 0.2 V.

HM5164165A/HM5165165A Series

Capacitance ($T_a = 25^\circ\text{C}$, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$)

Parameter	Symbol	Typ	Max	Unit	Notes
Input capacitance (Address)	C_{i1}	—	5	pF	1
Input capacitance (Clocks)	C_{i2}	—	7	pF	1
Output capacitance (Data-in, Data-out)	C_{io}	—	7	pF	1, 2

Notes : 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.

2. $\overline{\text{RAS}}$, $\overline{\text{UCAS}}$ and $\overline{\text{LCAS}} = V_{IH}$ to disable Dout.

HITACHI

13

■ 4496203 0033222 490 ■

HM5164165A/HM5165165A Series

AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $V_{SS} = 0 \text{ V}$)*¹, *², *¹⁸, *¹⁹, *²⁰

Test Conditions

- Input rise and fall time: 2 ns
- Input levels: 0 V, 3.0 V
- Input timing reference levels: 0.8 V, 2.0 V
- Output timing reference levels: 0.8 V, 2.0 V
- Output load: 1 TTL gate + C_L (100 pF) (Including scope and jig)

Read, Write, Read-Modify-Write and Refresh Cycles (Common parameters)

		HM5164165A/HM5165165A							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Random read or write cycle time	t_{RC}	TBD	—	104	—	124	—	ns	
RAS precharge time	t_{RP}	TBD	—	40	—	50	—	ns	
CAS precharge time	t_{CP}	TBD	—	10	—	13	—	ns	
RAS pulse width	t_{RAS}	TBD	TBD	60	10000	70	10000	ns	
CAS pulse width	t_{CAS}	TBD	TBD	10	10000	13	10000	ns	
Row address setup time	t_{ASR}	TBD	—	0	—	0	—	ns	
Row address hold time	t_{RAH}	TBD	—	10	—	10	—	ns	
Column address setup time	t_{ASC}	TBD	—	0	—	0	—	ns	21
Column address hold time	t_{CAH}	TBD	—	10	—	13	—	ns	21
RAS to CAS delay time	t_{RCD}	TBD	TBD	20	45	20	52	ns	3
RAS to column address delay time	t_{RAD}	TBD	TBD	15	30	15	35	ns	4
RAS hold time	t_{RSH}	TBD	—	15	—	18	—	ns	
CAS hold time	t_{CSH}	TBD	—	48	—	58	—	ns	23
CAS to RAS precharge time	t_{CRP}	TBD	—	5	—	5	—	ns	22
OE to Din delay time	t_{OED}	TBD	—	15	—	18	—	ns	5
OE delay time from Din	t_{DZO}	TBD	—	0	—	0	—	ns	6
CAS delay time from Din	t_{DZC}	TBD	—	0	—	0	—	ns	6
Transition time (rise and fall)	t_T	TBD	TBD	2	50	2	50	ns	7

HM5164165A/HM5165165A Series

Read Cycle

		HM5164165A/HM5165165A							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Access time from $\overline{\text{RAS}}$	t_{RAC}	—	TBD	—	60	—	70	ns	8, 9
Access time from $\overline{\text{CAS}}$	t_{CAC}	—	TBD	—	15	—	18	ns	9, 10, 17
Access time from address	t_{AA}	—	TBD	—	30	—	35	ns	9, 11, 17
Access time from $\overline{\text{OE}}$	t_{OEA}	—	TBD	—	15	—	18	ns	9
Read command setup time	t_{RCS}	TBD	—	0	—	0	—	ns	21
Read command hold time to $\overline{\text{CAS}}$	t_{RCH}	TBD	—	0	—	0	—	ns	12, 22
Read command hold time from $\overline{\text{RAS}}$	t_{RCHR}	TBD	—	60	—	70	—	ns	
Read command hold time to $\overline{\text{RAS}}$	t_{RRH}	TBD	—	0	—	0	—	ns	12
Column address to $\overline{\text{RAS}}$ lead time	t_{RAL}	TBD	—	30	—	35	—	ns	
Column address to $\overline{\text{CAS}}$ lead time	t_{CAL}	TBD	—	18	—	23	—	ns	
$\overline{\text{CAS}}$ to output in low-Z	t_{CLZ}	TBD	—	0	—	0	—	ns	
Output data hold time	t_{OH}	TBD	—	3	—	3	—	ns	27
Output data hold time from $\overline{\text{OE}}$	t_{OHO}	TBD	—	3	—	3	—	ns	
Output buffer turn-off time	t_{OFF}	—	TBD	—	15	—	15	ns	13, 27
Output buffer turn-off to $\overline{\text{OE}}$	t_{OEZ}	—	TBD	—	15	—	15	ns	13
$\overline{\text{CAS}}$ to Din delay time	t_{CDD}	TBD	—	15	—	18	—	ns	5
Output data hold time from $\overline{\text{RAS}}$	t_{OHR}	TBD	—	3	—	3	—	ns	27
Output buffer turn-off to $\overline{\text{RAS}}$	t_{OFR}	—	TBD	—	15	—	15	ns	27
Output buffer turn-off to $\overline{\text{WE}}$	t_{WEZ}	—	TBD	—	15	—	15	ns	
$\overline{\text{WE}}$ to Din delay time	t_{WED}	TBD	—	15	—	18	—	ns	
$\overline{\text{RAS}}$ to Din delay time	t_{RDD}	TBD	—	15	—	18	—	ns	

HITACHI

15

■ 4496203 0033224 263 ■

HM5164165A/HM5165165A Series

Write Cycle

		HM5164165A/HM5165165A							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Write command setup time	t_{WCS}	TBD	—	0	—	0	—	ns	14, 21
Write command hold time	t_{WCH}	TBD	—	10	—	13	—	ns	21
Write command pulse width	t_{WP}	TBD	—	10	—	10	—	ns	
Write command to $\overline{RAS}$ lead time	t_{RWL}	TBD	—	10	—	13	—	ns	
Write command to $\overline{CAS}$ lead time	t_{CWL}	TBD	—	10	—	13	—	ns	23
Data-in setup time	t_{DS}	TBD	—	0	—	0	—	ns	15, 23
Data-in hold time	t_{DH}	TBD	—	10	—	13	—	ns	15, 23

Read-Modify-Write Cycle

		HM5164165A/HM5165165A							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Read-modify-write cycle time	t_{RWC}	TBD	—	149	—	175	—	ns	
$\overline{RAS}$ to $\overline{WE}$ delay time	t_{RWD}	TBD	—	78	—	91	—	ns	14
$\overline{CAS}$ to $\overline{WE}$ delay time	t_{CWD}	TBD	—	33	—	39	—	ns	14
Column address to $\overline{WE}$ delay time	t_{AWD}	TBD	—	48	—	56	—	ns	14
$\overline{OE}$ hold time from $\overline{WE}$	t_{OEH}	TBD	—	15	—	18	—	ns	

Refresh Cycle

		HM5164165A/HM5165165A							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
$\overline{CAS}$ setup time (CBR refresh cycle)	t_{CSR}	TBD	—	5	—	5	—	ns	21
$\overline{CAS}$ hold time (CBR refresh cycle)	t_{CHR}	TBD	—	10	—	10	—	ns	22
$\overline{WE}$ setup time (CBR refresh cycle)	t_{WRP}	TBD	—	0	—	0	—	ns	
$\overline{WE}$ hold time (CBR refresh cycle)	t_{WRH}	TBD	—	10	—	10	—	ns	
$\overline{RAS}$ precharge to $\overline{CAS}$ hold time	t_{RPC}	TBD	—	0	—	0	—	ns	21

HM5164165A/HM5165165A Series

EDO Page Mode Cycle

		HM5164165A/HM5165165A							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
EDO page mode cycle time	t _{HPC}	TBD	—	25	—	30	—	ns	25
EDO page mode $\overline{\text{RAS}}$ pulse width	t _{RASP}	—	TBD	—	100000	—	100000	ns	16
Access time from $\overline{\text{CAS}}$ precharge	t _{CPA}	—	TBD	—	35	—	40	ns	9, 17
$\overline{\text{RAS}}$ hold time from $\overline{\text{CAS}}$ precharge	t _{CPRH}	TBD	—	35	—	40	—	ns	
Output data hold time from $\overline{\text{CAS}}$ low	t _{DOH}	TBD	—	3	—	3	—	ns	9, 17
$\overline{\text{CAS}}$ hold time referred $\overline{\text{OE}}$	t _{COL}	TBD	—	10	—	13	—	ns	
$\overline{\text{CAS}}$ to $\overline{\text{OE}}$ setup time	t _{COP}	TBD	—	10	—	10	—	ns	
Read command hold time from $\overline{\text{CAS}}$ precharge	t _{RCHC}	TBD	—	35	—	40	—	ns	
Write pulse width during $\overline{\text{CAS}}$ precharge	t _{WPE}	TBD	—	10	—	10	—	ns	
$\overline{\text{OE}}$ precharge time	t _{OEP}	TBD	—	10	—	10	—	ns	

EDO Page Mode Read-Modify-Write Cycle

		HM5164165A/HM5165165A							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
EDO page mode read-modify-write cycle time	t _{HPRWC}	TBD	—	68	—	79	—	ns	
WE delay time from CAS precharge	t _{CPW}	TBD	—	54	—	62	—	ns	14

Refresh (HM5164165A Series)

Parameter	Symbol	Max	Unit	Note
Refresh period	t_{REF}	64	ms	8192 cycles
Refresh period (L-version)	t_{REF}	TBD	ms	8192 cycles

HM5164165A/HM5165165A Series

Refresh (HM5165165A Series)

Parameter	Symbol	Max	Unit	Note
Refresh period	t_{REF}	64	ms	4096 cycles
Refresh period (L-version)	t_{REF}	128	ms	4096 cycles

HM5164165A/HM5165165A Series

Self Refresh Mode (L-version)

		HM5165165AL							
		-5		-6		-7			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
RAS pulse width (self refresh)	t_{RASS}	TBD	—	100	—	100	—	μs	
RAS precharge time (self refresh)	t_{RPS}	TBD	—	110	—	130	—	ns	
CAS hold time (self refresh)	t_{CHS}	TBD	—	-50	—	-50	—	ns	

Notes: 1. AC measurements assume $t_I = 2$ ns.

2. An initial pause of 200 μs is required after power up followed by a minimum of eight initialization cycles (any combination of cycles containing RAS-only refresh or CAS-before-RAS refresh).
3. Operation with the t_{RCD} (max) limit insures that t_{RAC} (max) can be met, t_{RCD} (max) is specified as a reference point only; if t_{RCD} is greater than the specified t_{RCD} (max) limit, then the access time is controlled exclusively by t_{CAC} .
4. Operation with the t_{RAD} (max) limit insures that t_{RAC} (max) can be met, t_{RAD} (max) is specified as a reference point only; if t_{RAD} is greater than the specified t_{RAD} (max) limit, then access time is controlled exclusively by t_{AA} .
5. Either t_{OED} or t_{CDD} must be satisfied.
6. Either t_{DZO} or t_{DZC} must be satisfied.
7. V_{IH} (min) and V_{IL} (max) are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} (min) and V_{IL} (max).
8. Assumes that $t_{RCD} \leq t_{RCD}$ (max) and $t_{RAD} \leq t_{RAD}$ (max). If t_{RCD} or t_{RAD} is greater than the maximum recommended value shown in this table, t_{RAC} exceeds the value shown.
9. Measured with a load circuit equivalent to 1 TTL loads and 100 pF.
10. Assumes that $t_{RCD} \geq t_{RCD}$ (max) and $t_{RCD} + t_{CAC}$ (max) $\geq t_{RAD} + t_{AA}$ (max).
11. Assumes that $t_{RAD} \geq t_{RAD}$ (max) and $t_{RCD} + t_{CAC}$ (max) $\leq t_{RAD} + t_{AA}$ (max).
12. Either t_{RCH} or t_{RRH} must be satisfied for a read cycles.
13. t_{OFF} (max), t_{OEZ} (max), t_{WEZ} (max) and t_{OFR} (max) define the time at which the outputs achieve the open circuit condition and are not referred to output voltage levels.
14. t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} and t_{CPW} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only; if $t_{WCS} \geq t_{WCS}$ (min), the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) throughout the entire cycle; if $t_{RWD} \geq t_{RWD}$ (min), $t_{CWD} \geq t_{CWD}$ (min), and $t_{AWD} \geq t_{AWD}$ (min), or $t_{CWD} \geq t_{CWD}$ (min), $t_{AWD} \geq t_{AWD}$ (min) and $t_{CPW} \geq t_{CPW}$ (min), the cycle is a read-modify-write and the data output will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
15. These parameters are referred to $\overline{UCAS}$ and $\overline{LCAS}$ leading edge in early write cycles and to $\overline{WE}$ leading edge in delayed write or read-modify-write cycles.
16. t_{RASP} defines $\overline{RAS}$ pulse width in EDO page mode cycles.
17. Access time is determined by the longest among t_{AA} , t_{CAC} and t_{CPA} .
18. When both $\overline{UCAS}$ and $\overline{LCAS}$ go low at the same time, all 16-bit data are written into the device. $\overline{UCAS}$ and $\overline{LCAS}$ cannot be staggered within the same write/read cycles.
19. All the V_{CC} and V_{SS} pins shall be supplied with the same voltages.
20. In delayed write or read-modify-write cycles, $\overline{OE}$ must disable output buffer prior to applying data to the device.
21. t_{ASC} , t_{CAH} , t_{RCS} , t_{WCS} , t_{WCH} , t_{CSR} and t_{RPC} are determined by the earlier falling edge of $\overline{UCAS}$ or $\overline{LCAS}$.
22. t_{CRP} , t_{CHR} , t_{RCH} , t_{CPA} and t_{CPW} are determined by the later rising edge of $\overline{UCAS}$ or $\overline{LCAS}$.
23. t_{CWL} , t_{DH} , t_{DS} and t_{CSH} should be satisfied by both $\overline{UCAS}$ and $\overline{LCAS}$.

HITACHI

19

■ 4496203 0033228 909 ■

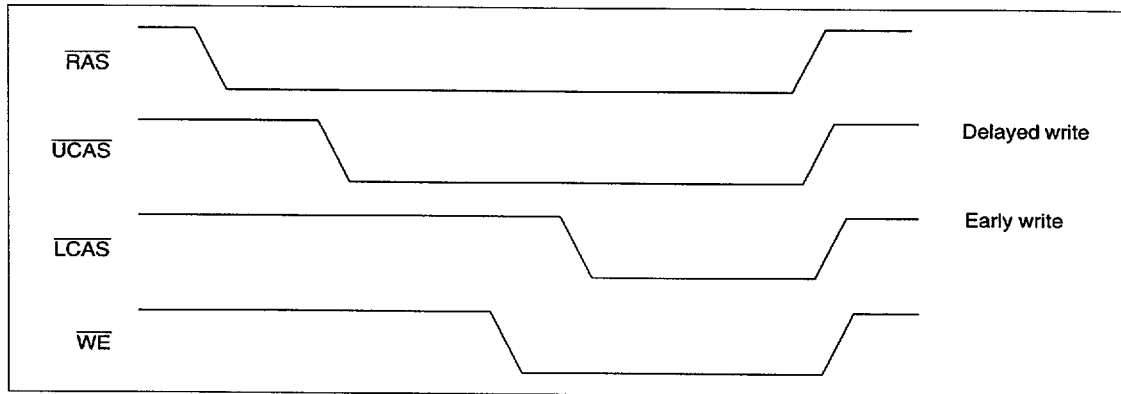
HM5164165A/HM5165165A Series

24. t_{CP} is determined by the time that both $\overline{UCAS}$ and $\overline{LCAS}$ are high.
25. t_{HPC} (min) can be achieved during a series of EDO page mode write cycles or EDO page mode read cycles. If both write and read operation are mixed in a EDO page mode $\overline{RAS}$ cycle (EDO page mode mix cycle (1), (2)), minimum value of $\overline{CAS}$ cycle ($t_{CAS} + t_{CP} + 2 t_T$) becomes greater than the specified t_{HPC} (min) value. The value of $\overline{CAS}$ cycle time of mixed EDO page mode is shown in EDO page mode mix cycle (1) and (2).
26. When output buffers are enabled once, sustain the low impedance state until valid data is obtained. When output buffer is turned on and off within a very short time, generally it causes large V_{CC}/V_{SS} line noise, which causes to degrade V_{IH} min/ V_{IL} max level.
27. Data output turns off and becomes high impedance from later rising edge of $\overline{RAS}$ and $\overline{CAS}$. Hold time and turn off time are specified by the timing specifications of later rising edge of $\overline{RAS}$ and $\overline{CAS}$ between t_{OHR} and t_{OH} , and between t_{OFR} and t_{OFF} .
28. Please do not use t_{RASS} timing, $10 \mu s \leq t_{RASS} \leq 100 \mu s$. During this period, the device is in transition state from normal operation mode to self refresh mode. If $t_{RASS} \geq 100 \mu s$, then $\overline{RAS}$ precharge time should use t_{RPS} instead of t_{RP} .
29. CBR burst refresh or 4096 cycles of distributed CBR refresh with $15.6 \mu s$ interval should be executed within 64 ms immediately after exiting from and before entering into the self refresh mode.
30. Repetitive self refresh mode without refreshing all memory is not allowed. Once you exit from self refresh mode, all memory cells need to be refreshed before re-entering the self refresh mode again.
31. XXX: H or L (H: $V_{IH} \text{ (min)} \leq V_{IN} \leq V_{IH} \text{ (max)}$, L: $V_{IL} \text{ (min)} \leq V_{IN} \leq V_{IL} \text{ (max)}$)
/////: Invalid Dout
When the address, clock and input pins are not described on timing waveforms, their pins must be applied V_{IH} or V_{IL} .

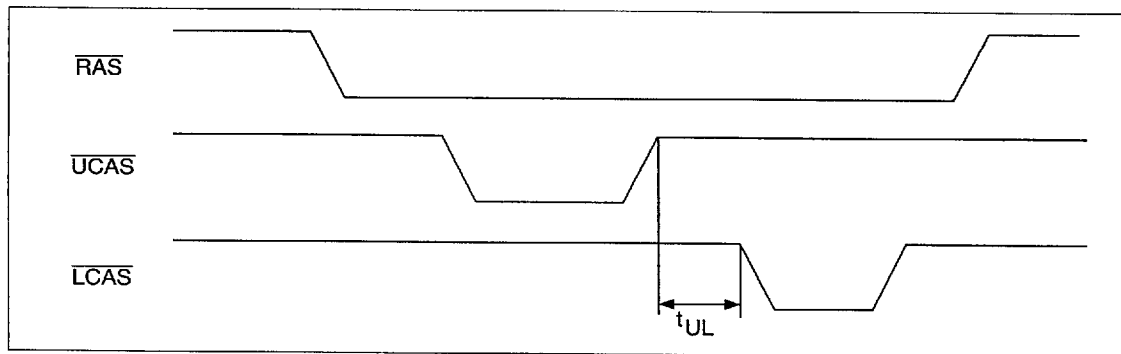
Notes concerning $\overline{2CAS}$ control

Please do not separate the $\overline{UCAS}/\overline{LCAS}$ operation timing intentionally. However skew between $\overline{UCAS}/\overline{LCAS}$ are allowed under the following conditions.

1. Each of the $\overline{UCAS}/\overline{LCAS}$ should satisfy the timing specifications individually.
2. Different operation mode for upper/lower byte is not allowed; such as following.



3. Closely separated upper/lower byte control is not allowed. However when the condition ($t_{CP} \leq t_{UL}$) is satisfied, EDO page mode can be performed.

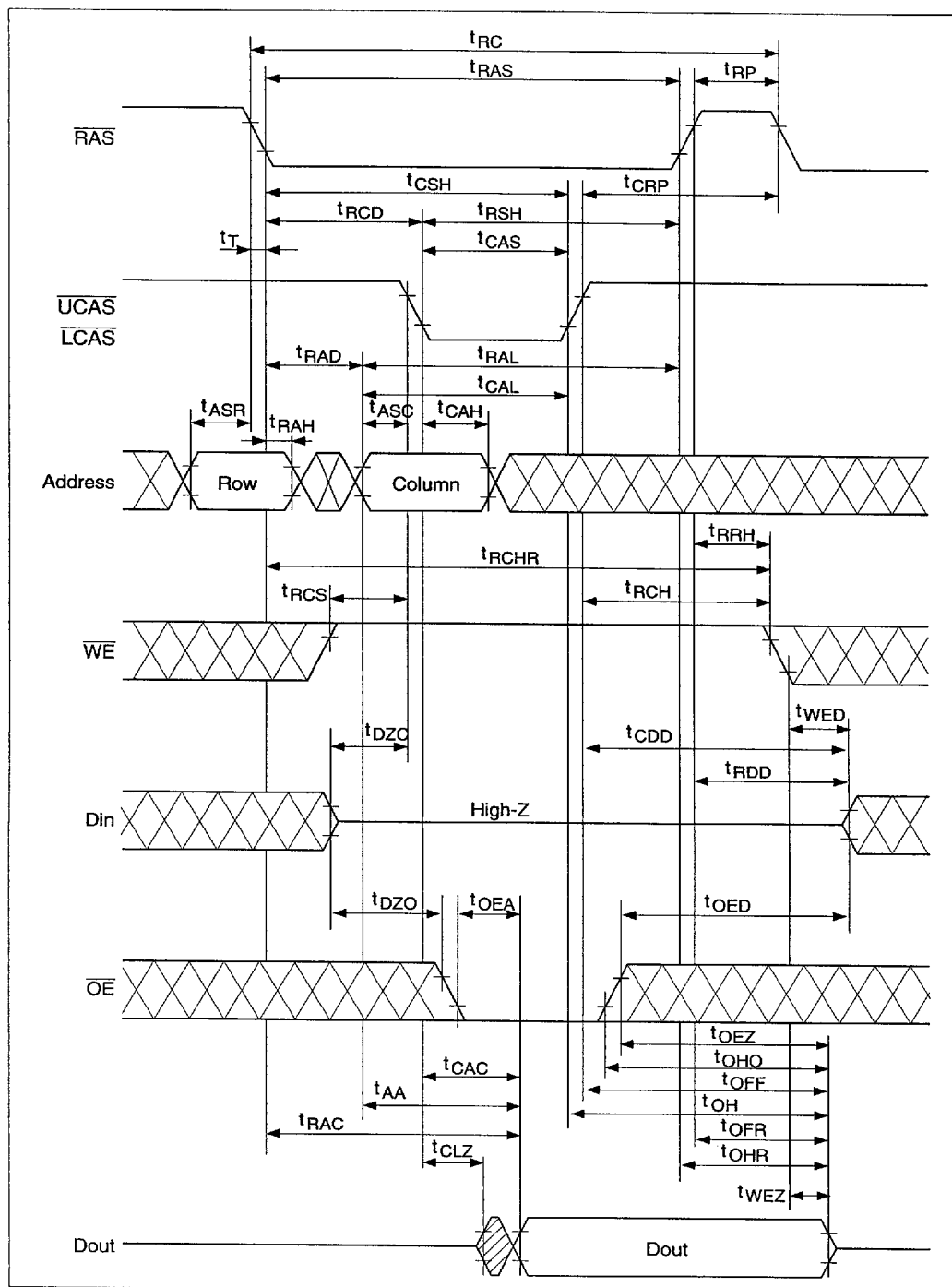


4. Byte control operation by remaining $\overline{UCAS}$ or $\overline{LCAS}$ high is guaranteed.

HM5164165A/HM5165165A Series

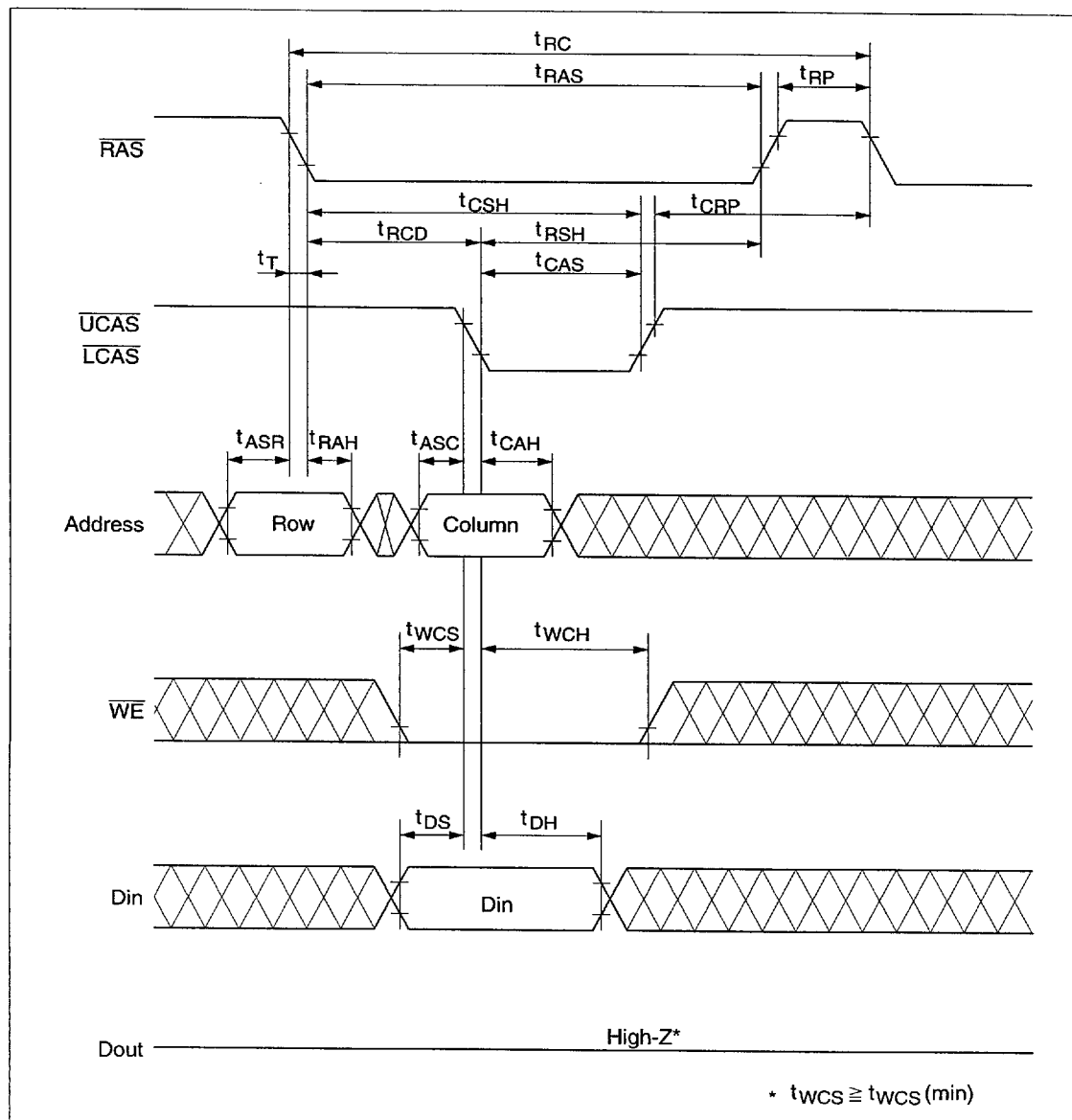
Timing Waveforms*31

Read Cycle

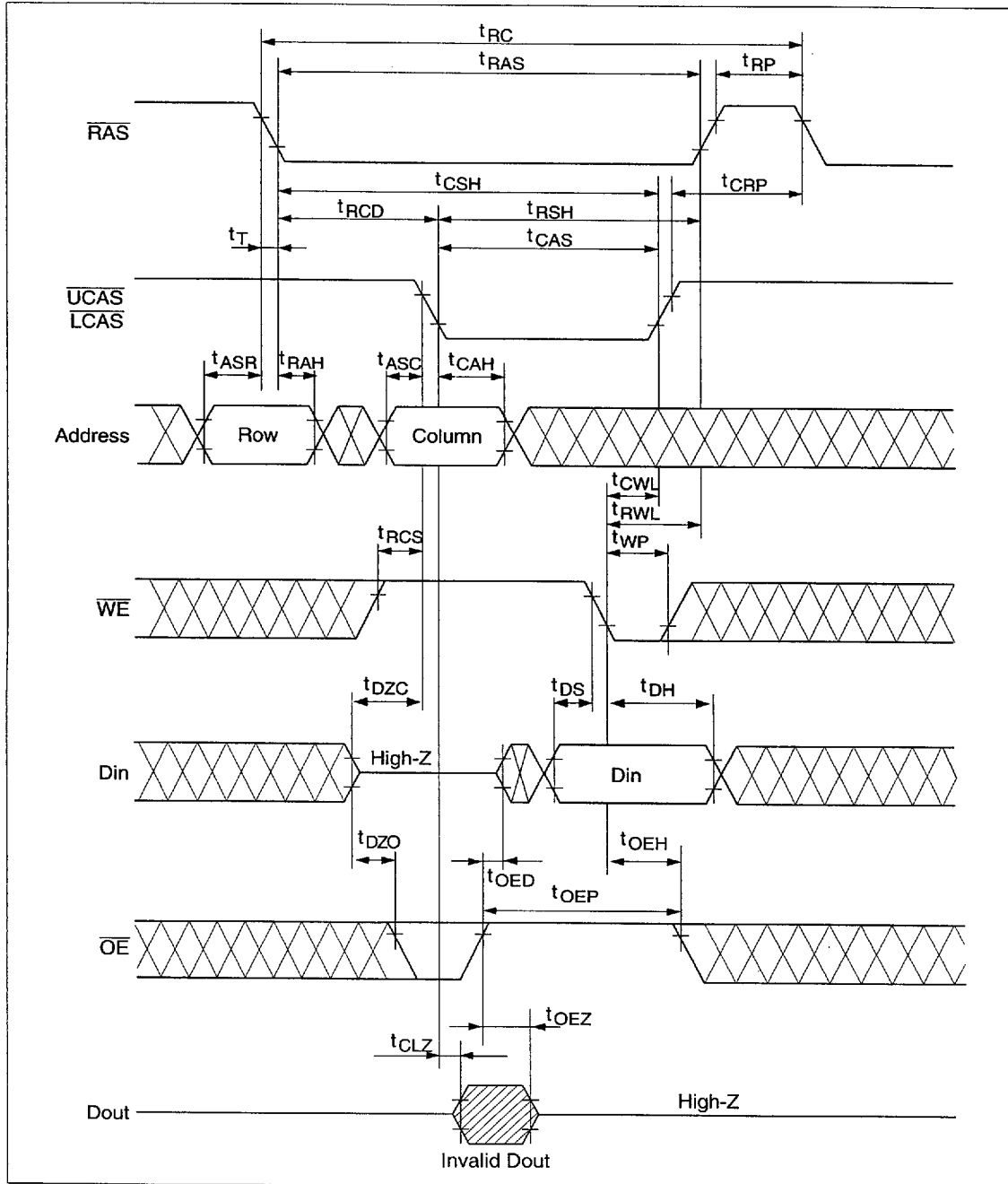


HM5164165A/HM5165165A Series

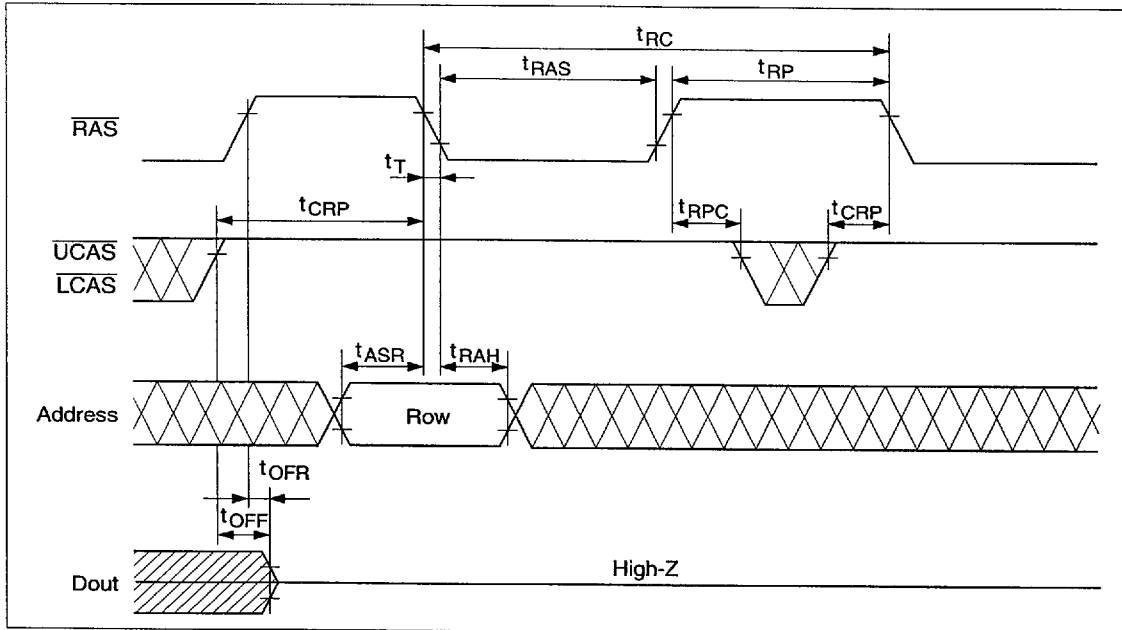
Early Write Cycle



Delayed Write Cycle*20

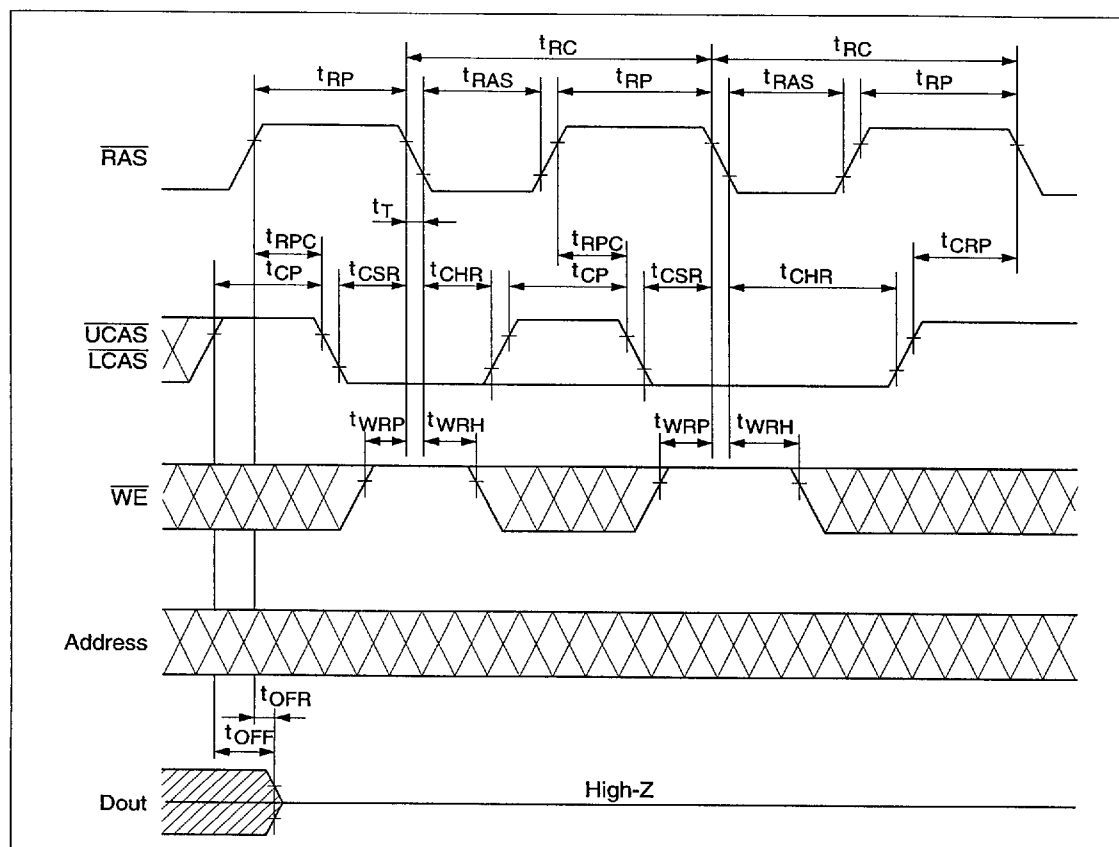


RAS-Only Refresh Cycle

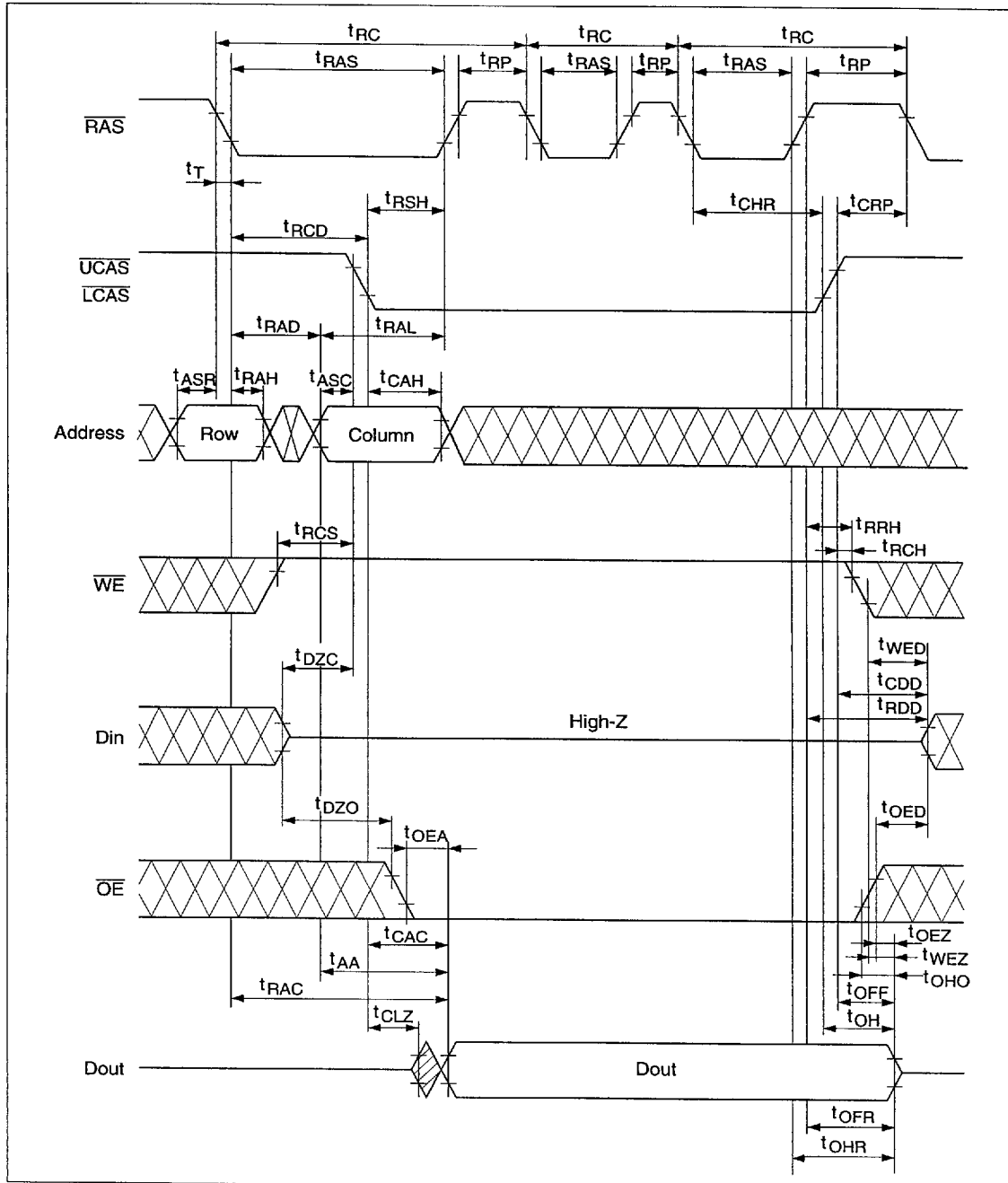


HM5164165A/HM5165165A Series

CAS-Before-RAS Refresh Cycle

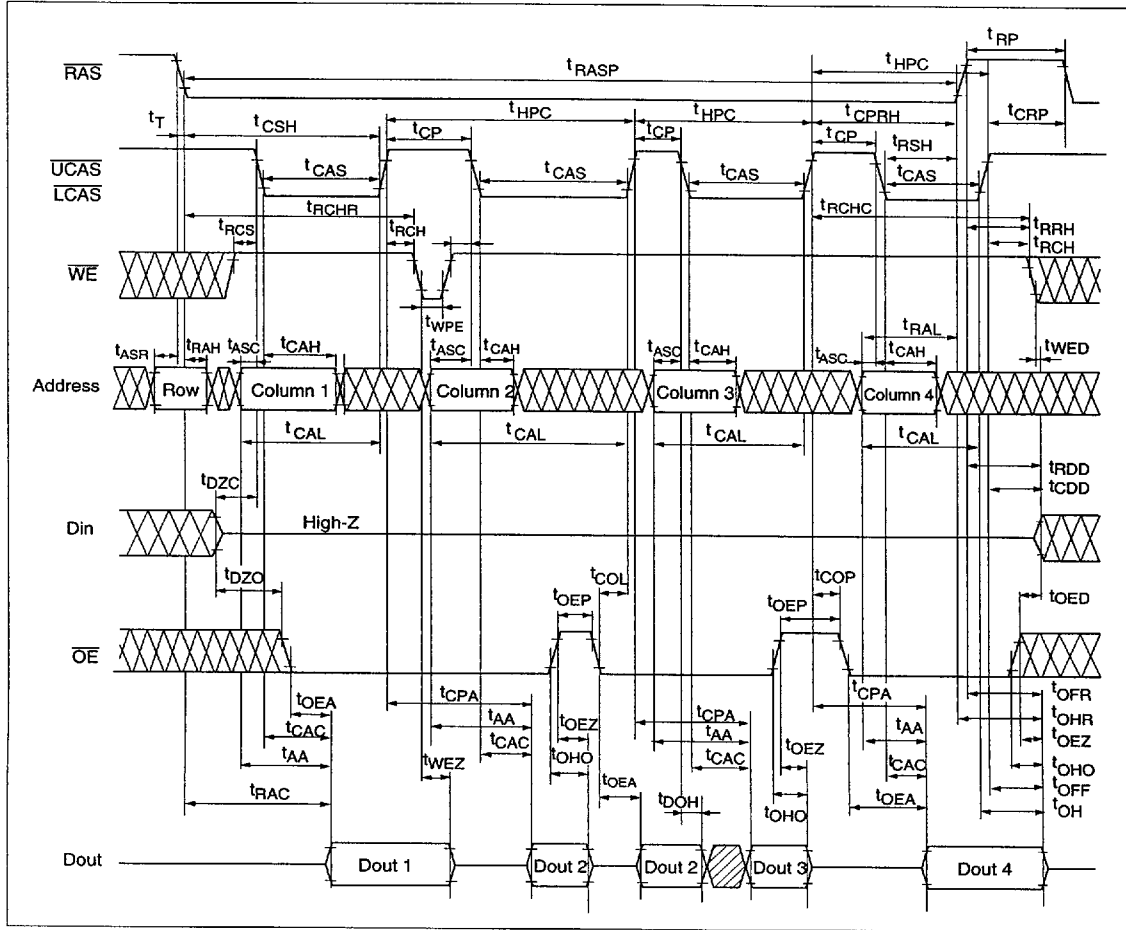


Hidden Refresh Cycle



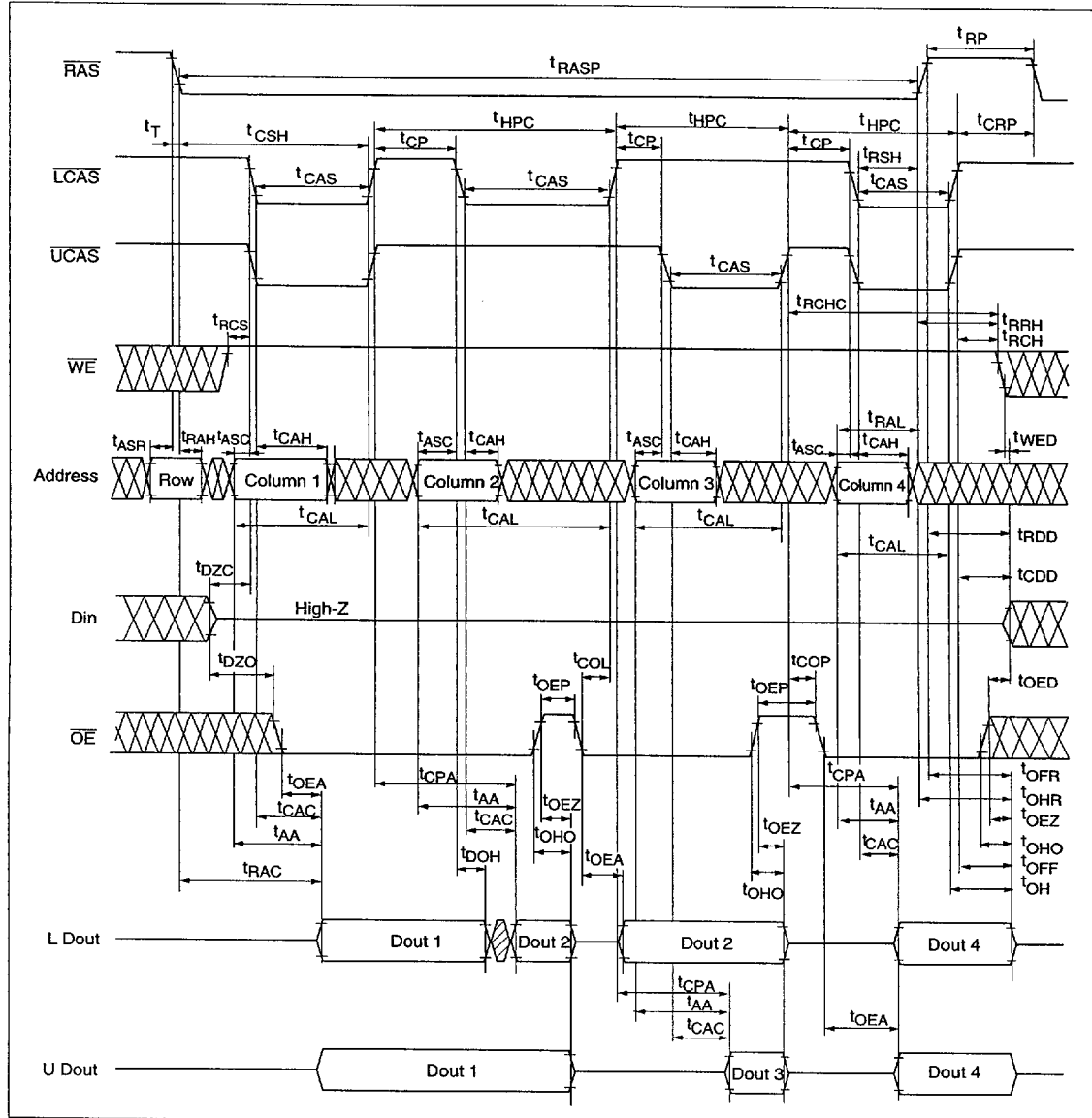
HM5164165A/HM5165165A Series

EDO Page Mode Read Cycle



HM5164165A/HM5165165A Series

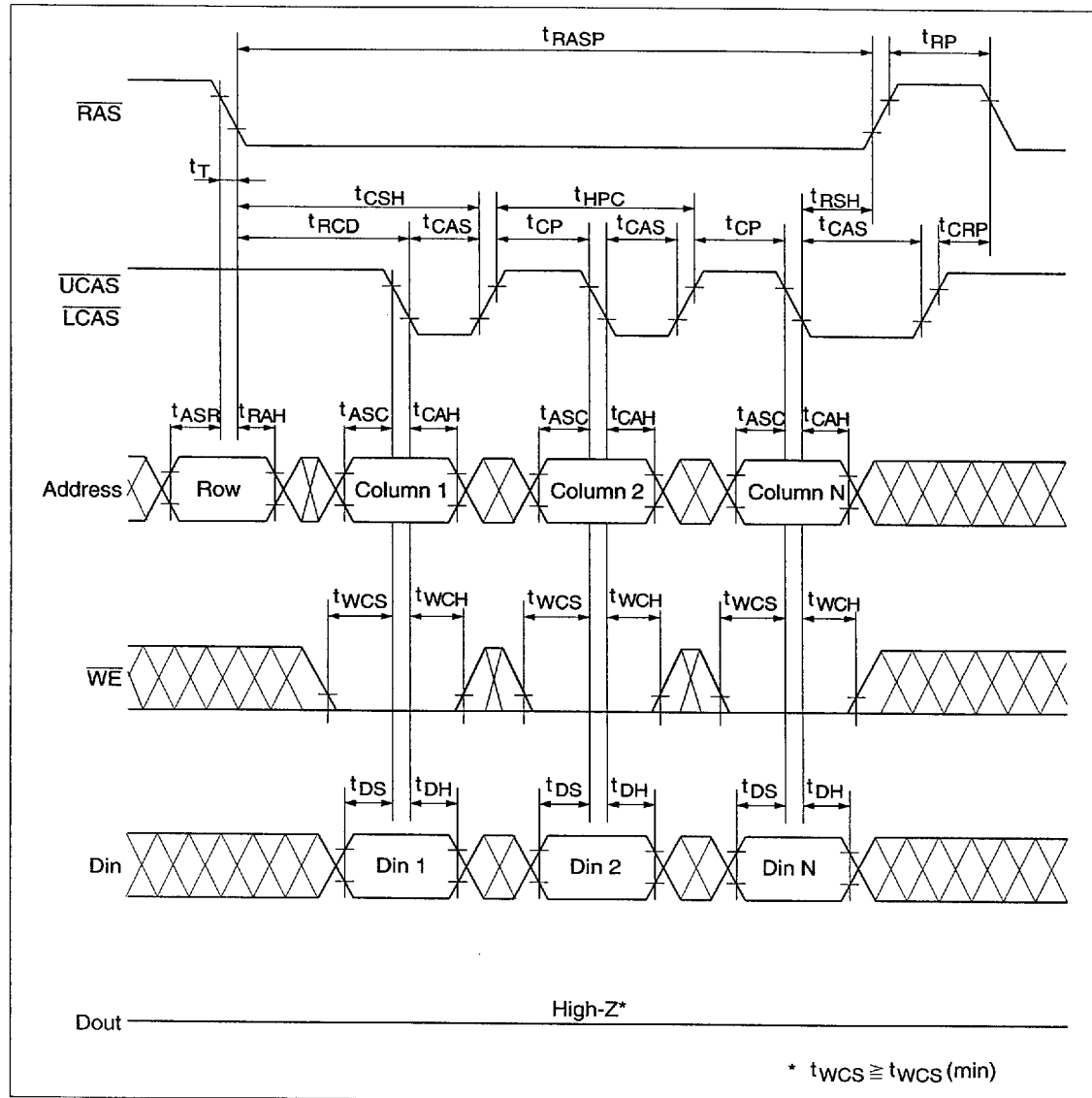
EDO Page Mode Read Cycle ($2\overline{\text{CAS}}$)



HITACHI

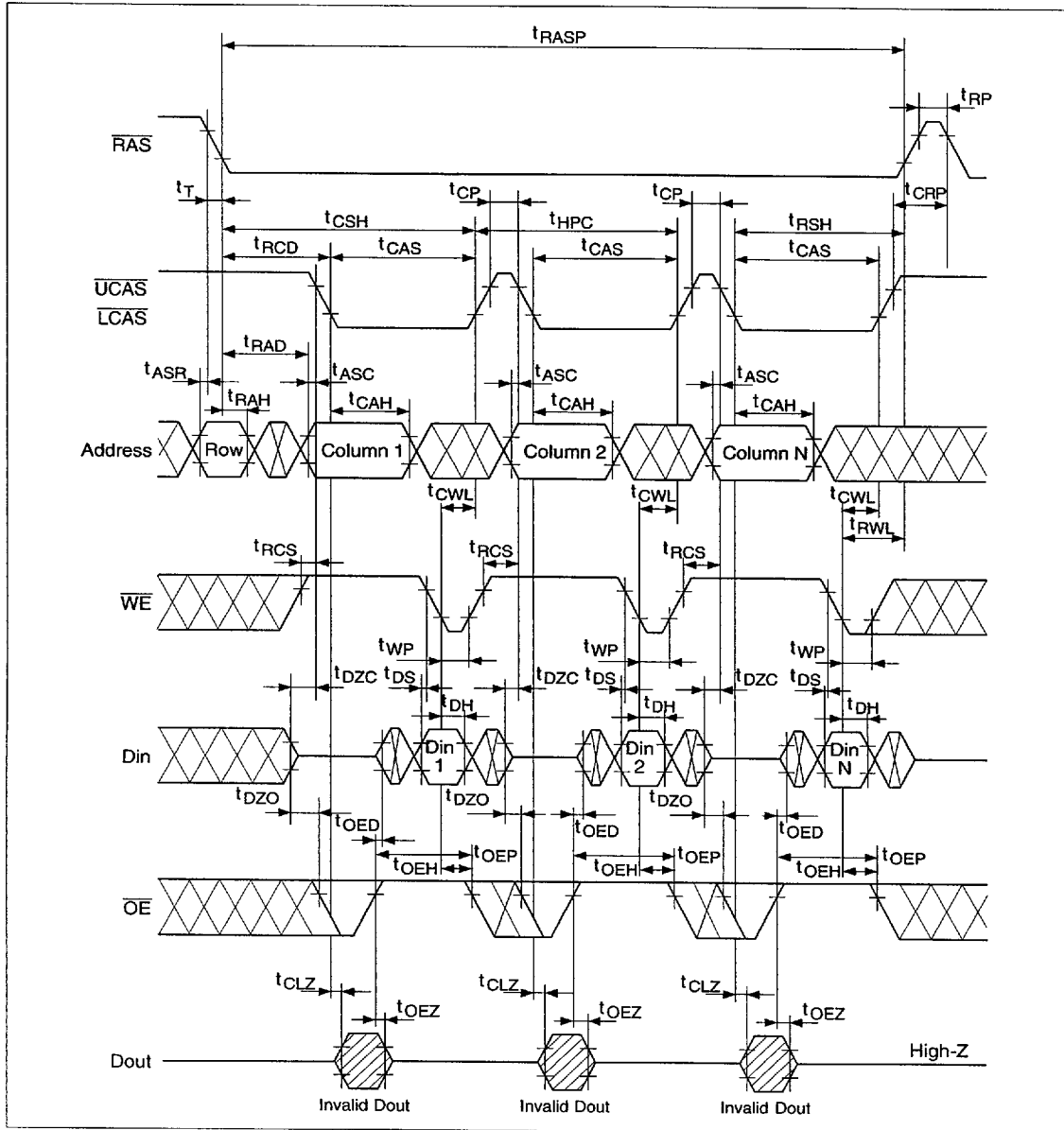
HM5164165A/HM5165165A Series

EDO Page Mode Early Write Cycle



HM5164165A/HM5165165A Series

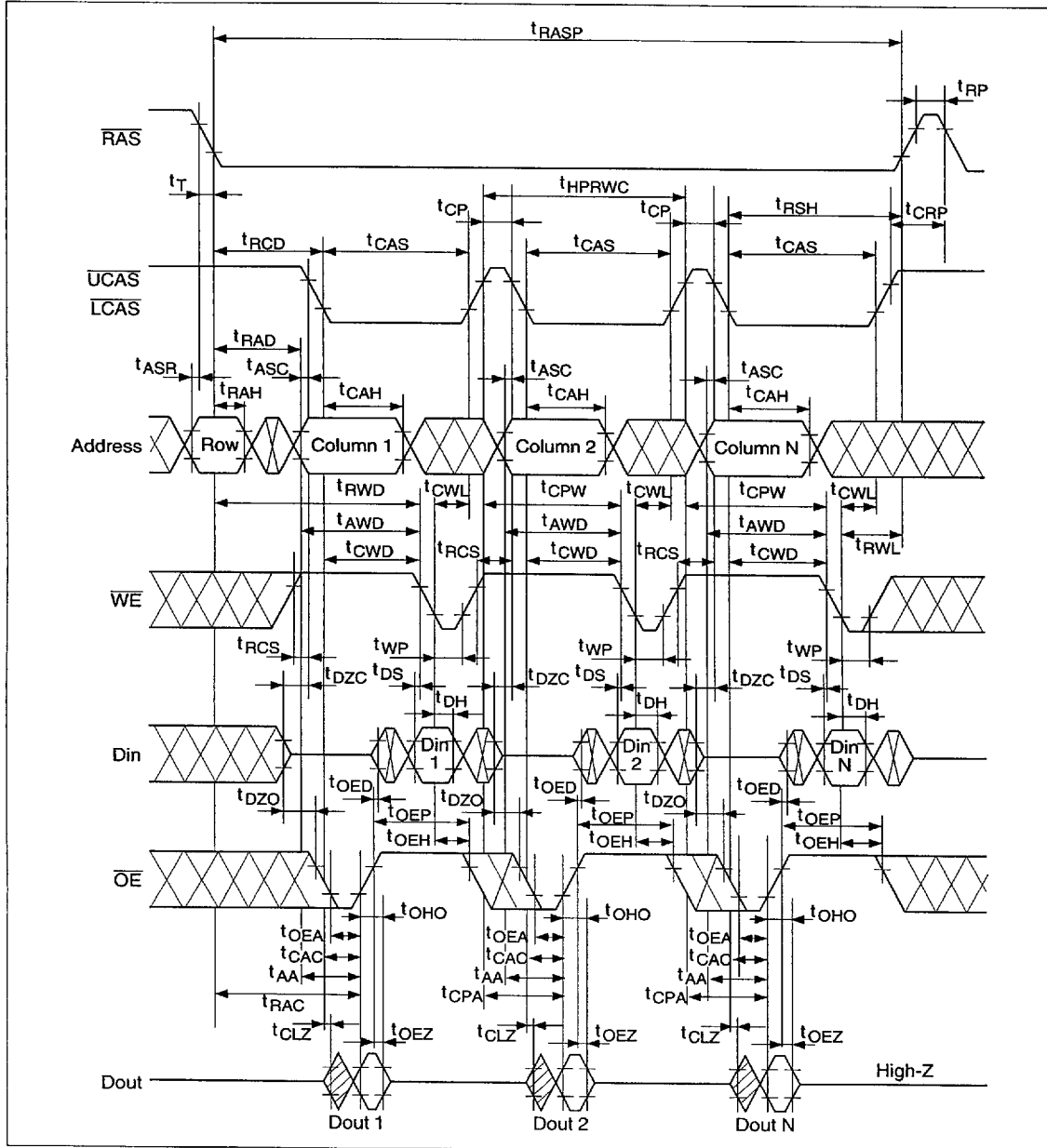
EDO Page Mode Delayed Write Cycle*20

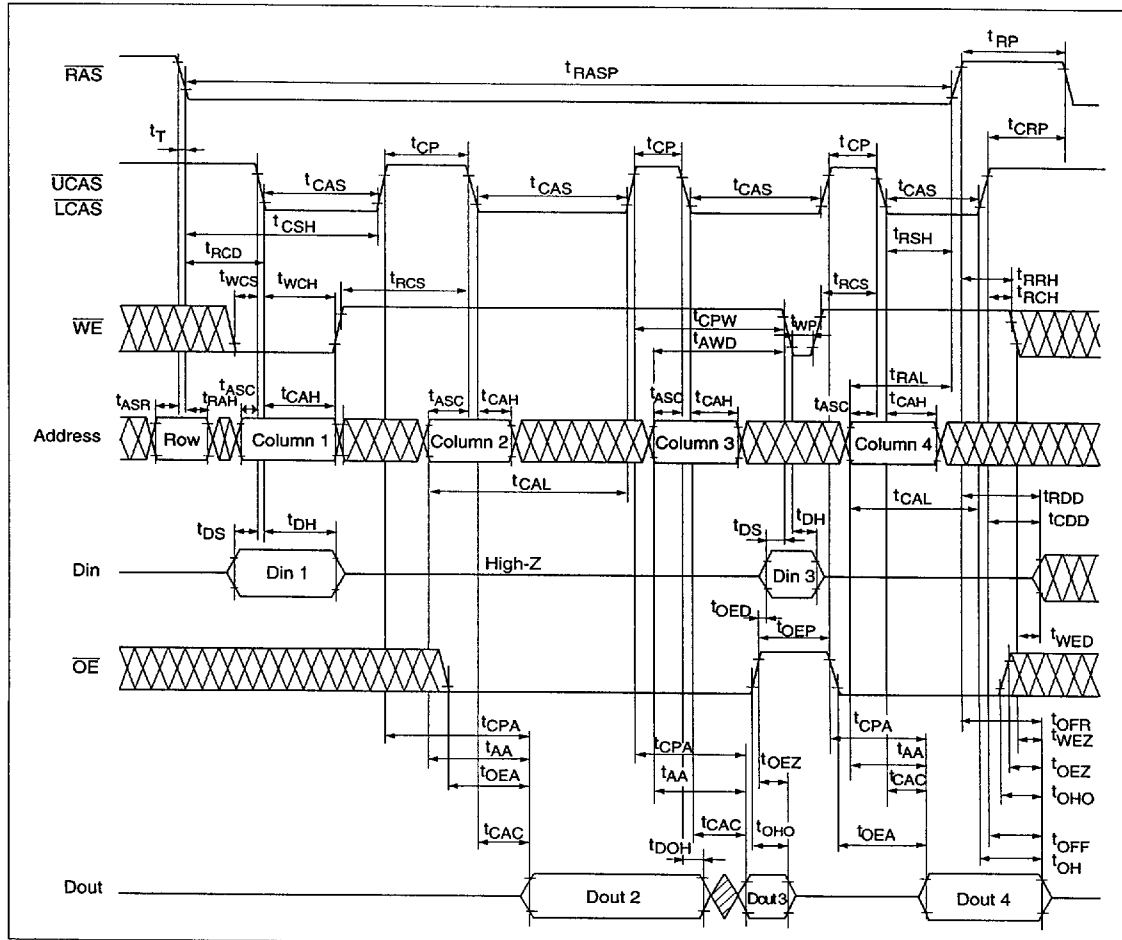


HITACHI

HM5164165A/HM5165165A Series

EDO Page Mode Read-Modify-Write Cycle*20



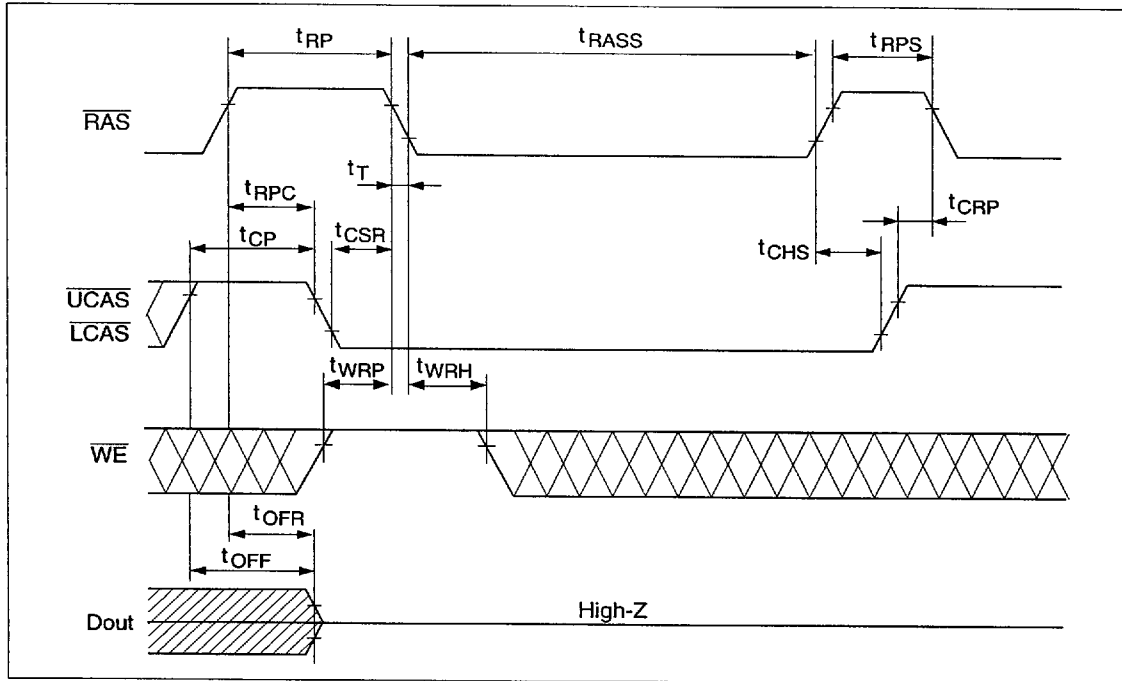


35

4496203 0033244 051

HM5164165A/HM5165165A Series

Self Refresh Cycle (L-version)*28, 29, 30



HITACHI

37

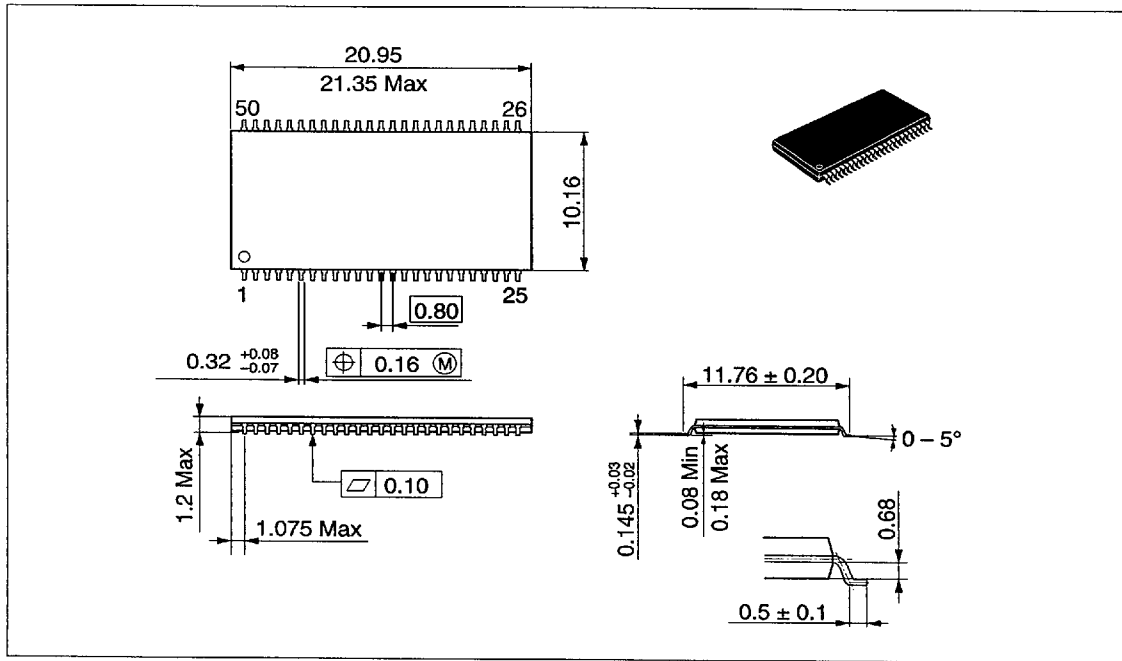
4496203 0033246 924

HM5164165A/HM5165165A Series

HM5164165ATT/ALTT Series

HM5165165ATT/ALTT Series (TTP-50DB)

Unit: mm



HITACHI

39

4496203 0033248 7T7